

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (currently amended): For semiconductor manufacturing equipment, a ceramic susceptor comprising:

having a ceramic substrate defining a wafer-support side; and

a resistive heating element composed of wiring lines, defining bottom and lateral sides, in a predetermined configuration provided on either a surface of or inside a said ceramic substrate, the ceramic susceptor for semiconductor manufacturing equipment characterized in that said resistive heating element being configured so that in section through said wiring lines the smallest angle formed by the bottom face and lateral faces of the resistive heating element in section sides is 5° or greater.

Claim 2 (currently amended): A ceramic susceptor ~~for semiconductor manufacturing equipment~~ as set forth in claim 1, ~~characterized in that~~ wherein when a wafer is placed on the wafer support ~~surface and the side and said~~ resistive heating element is drawing current and heated deviation in the wafer surface temperature is  $\pm 1.0\%$  or less at working temperature.

Claim 3 (currently amended): A ceramic susceptor ~~for semiconductor manufacturing equipment~~ as set forth in claim 2, ~~characterized in that~~ wherein deviation in the wafer surface temperature is within  $\pm 0.5\%$  at working temperature.

Claim 4 (currently amended): A ceramic susceptor ~~for semiconductor manufacturing equipment~~ as set forth in ~~any of claims 1 to 3, characterized in that the~~ claim 1, wherein said ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride and silicon carbide.

Claim 5 (currently amended): A ceramic susceptor ~~for semiconductor manufacturing equipment~~ as set forth in ~~any of claims 1 to 4, characterized in that the~~ claim 1, wherein said ceramic substrate is either aluminum nitride or silicon carbide of 100 W/m-K or greater thermal conductivity.

Claim 6 (currently amended): A ceramic susceptor~~for semiconductor manufacturing equipment~~ as set forth in ~~any of claims 1 to 5, characterized in that the~~ claim 1, wherein said resistive heating element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel and chrome.

Claim 7 (currently amended): A ceramic susceptor ~~for semiconductor manufacturing equipment~~ as set forth in ~~any of claims 1 to 4, characterized in that further~~ claim 1, further comprising a plasma electrode is disposed either on a surface of or inside ~~the~~ said ceramic substrate.

Claim 8 (new): A ceramic susceptor as set forth in claim 2, wherein said ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride and silicon carbide.

Claim 9 (new): A ceramic susceptor as set forth in claim 3, wherein said ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride and silicon carbide.

Claim 10 (new): A ceramic susceptor as set forth in claim 9, wherein said ceramic substrate is either aluminum nitride or silicon carbide of 100 W/m·K or greater thermal conductivity.

Claim 11 (new): A ceramic susceptor as set forth in claim 10, wherein said resistive heating element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel and chrome.

Claim 12 (new): A ceramic susceptor as set forth in any claim 2, further comprising a plasma electrode disposed either on a surface of or inside said ceramic substrate.

Claim 13 (new): A ceramic susceptor as set forth in any claim 4, further comprising a plasma electrode disposed either on a surface of or inside said ceramic substrate.

Claim 14 (new): A ceramic susceptor as set forth in any claim 11, further comprising a plasma electrode disposed either on a surface of or inside said ceramic substrate.